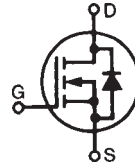


Polar™ Power MOSFET

HiPerFET™

IXFN52N90P

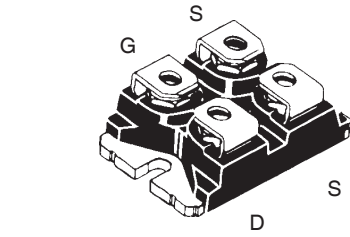
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$$\begin{aligned} V_{DSS} &= 900V \\ I_{D25} &= 43A \\ R_{DS(on)} &\leq 160m\Omega \\ t_{rr} &\leq 300ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	900	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	900	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	43	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	104	A
I_A	$T_C = 25^\circ\text{C}$	26	A
E_{AS}	$T_C = 25^\circ\text{C}$	2	J
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	20	V/ns
P_D	$T_C = 25^\circ\text{C}$	890	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6mm (0.062 in.) from case for 10s	300	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS	$t = 1\text{min}$	2500 V~
	$I_{ISOL} \leq 1\text{mA}$	$t = 1\text{s}$	3000 V~
M_d	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque	1.3/11.5	Nm/lb.in.
Weight		30	g

miniBLOC, SOT-227
E153432



G = Gate
S = Source
D = Drain

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Features

- International standard package
- miniBLOC, with Aluminium nitride isolation
- Avalanche Rated
- Low package inductance
- Fast intrinsic diode

Advantages

- Low gate drive requirement
- High power density

Applications:

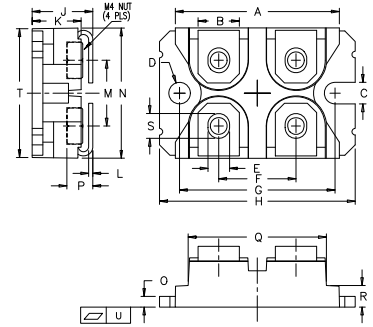
- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor drives
- Robotics and servo controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 3\text{mA}$	900		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1\text{mA}$	3.5		6.5 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$			50 μA
	$V_{GS} = 0V$, $T_J = 125^\circ\text{C}$			4 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 26A$, Note 1			160 m Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 26\text{A}$, Note 1	20	35	S
R_{Gi}	Gate input resistance		1.56	Ω
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		19	nF
C_{oss}			1180	pF
C_{rss}			24	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 26\text{A}$ $R_G = 1\Omega$ (External)		63	ns
t_r			80	ns
$t_{d(off)}$			95	ns
t_f			42	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 26\text{A}$		308	nC
Q_{gs}			117	nC
Q_{gd}			132	nC
R_{thJC}				0.14 $^\circ\text{C/W}$
R_{thCS}			0.05	$^\circ\text{C/W}$

Source-Drain Diode		Characteristic Values		
$T_J = 25^\circ\text{C}$ unless otherwise specified)		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			56 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			208 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 26\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$			300 ns
Q_{RM}			1.8	μC
I_{RM}			26	A

SOT-227B Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

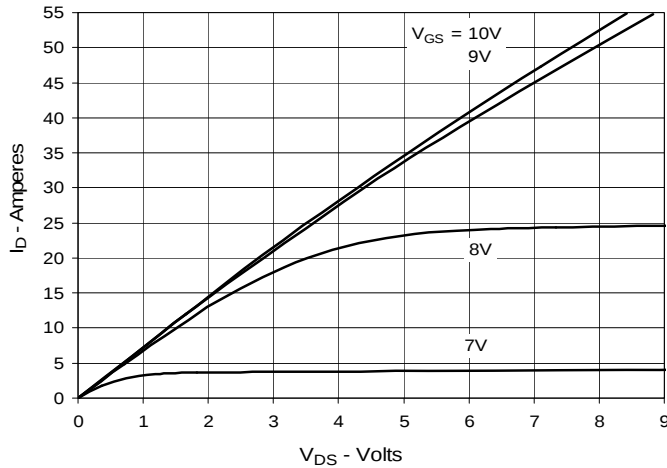
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

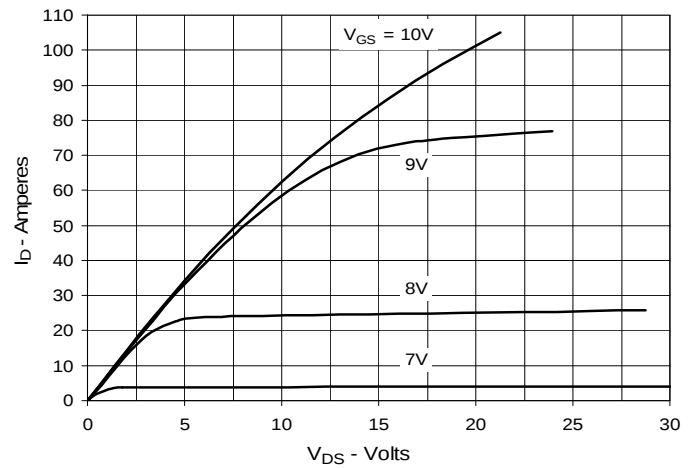
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

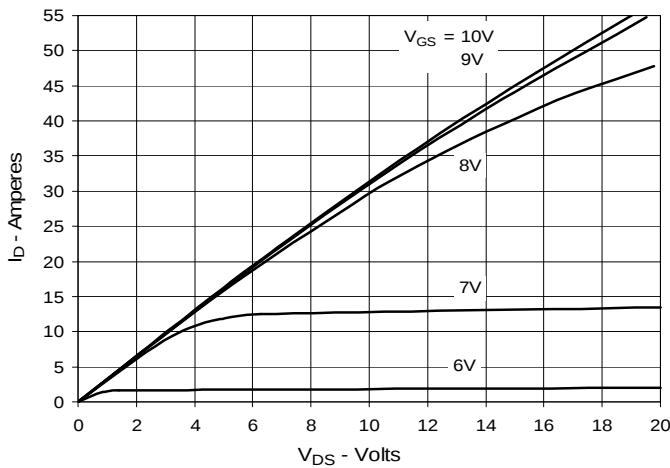
**Fig. 1. Output Characteristics
@ 25°C**



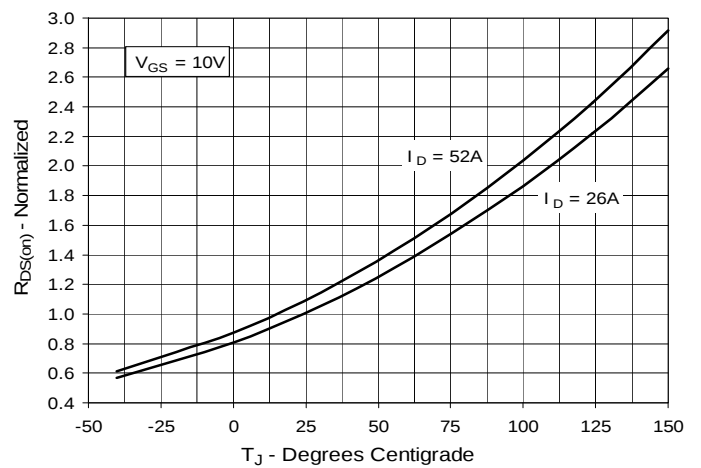
**Fig. 2. Extended Output Characteristics
@ 25°C**



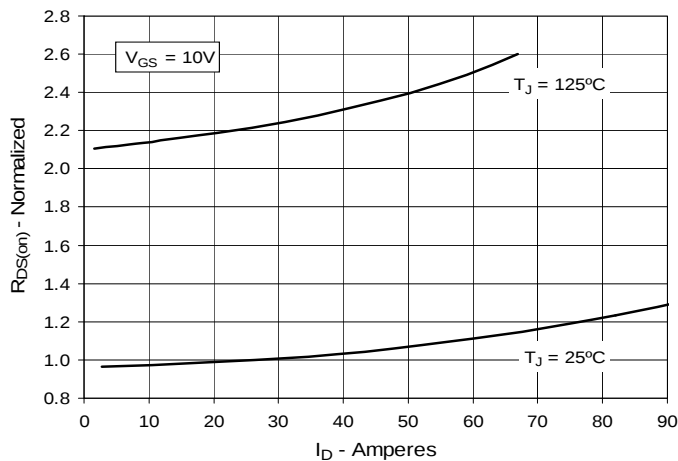
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 26A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 26A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

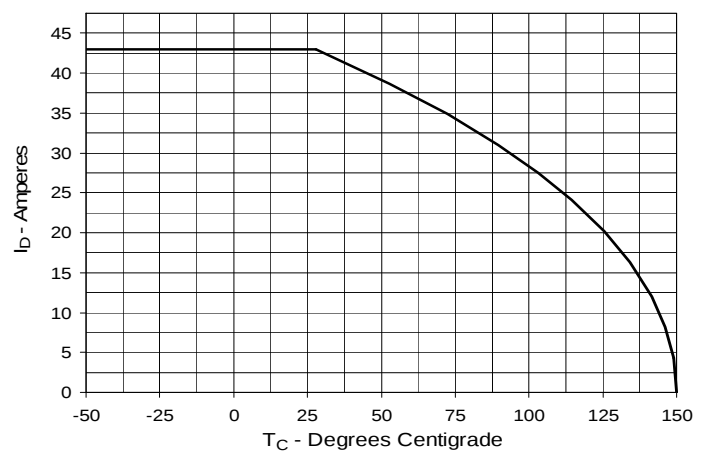
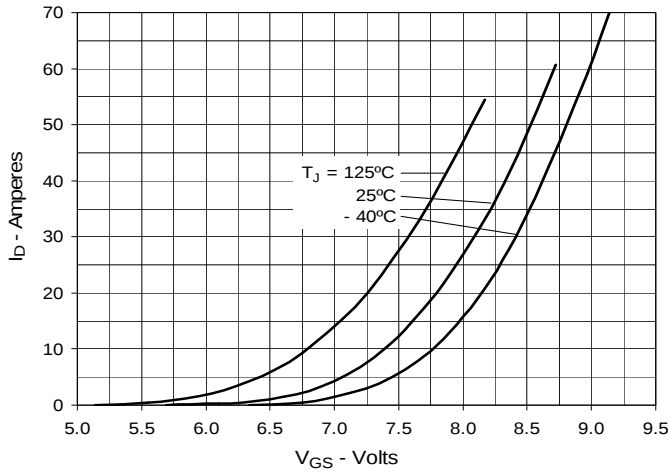
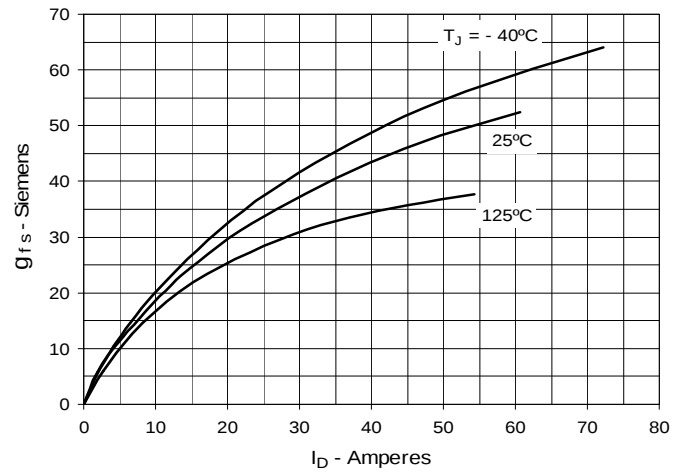
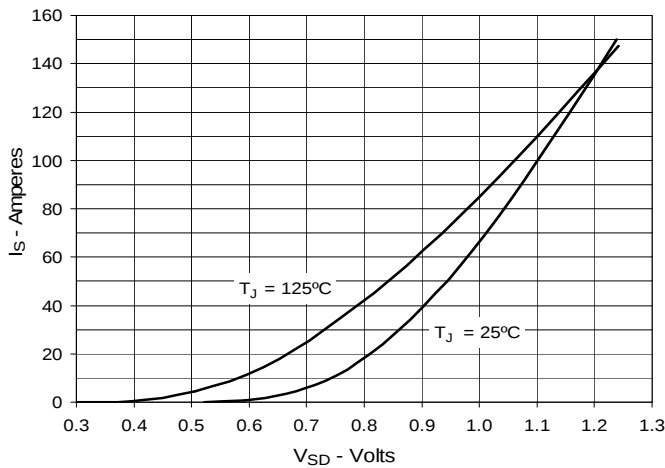
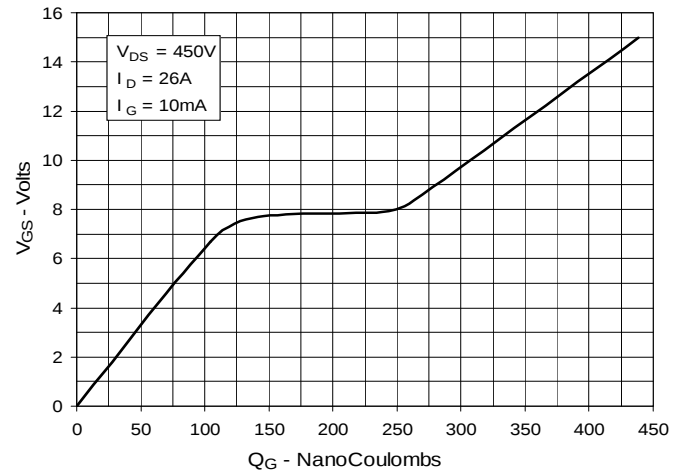
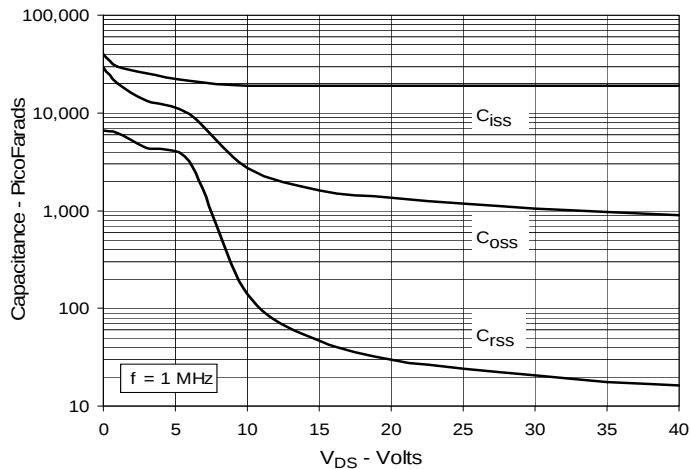


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance
